

#### **Features**

- Trench Power MV MOSFET Technology
- High Density Cell Design for Low R<sub>DS(on)</sub>
- · High Speed Switching
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note1)
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## **Maximum Ratings**

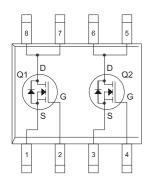
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 40.3°C/W Junction to Ambient (Note2)

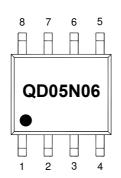
| Parameter                    | Symbol          | Rating | Unit |
|------------------------------|-----------------|--------|------|
| Drain-Source Voltage         | V <sub>DS</sub> | 60     | V    |
| Gate-Source Volltage         | $V_{GS}$        | ±20    | V    |
| Continuous Drain Current     | I <sub>D</sub>  | 5      | Α    |
| Pulsed Drain Current (Note3) | I <sub>DM</sub> | 25     | Α    |
| Total Power Dissipation      | P <sub>D</sub>  | 3.1    | W    |

#### Note:

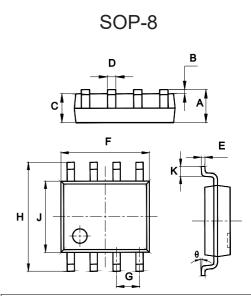
- 1.Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2.Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

# **Internal Structure and Marking Code**



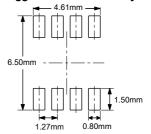


# Dual N-CHANNEL MOSFET



| DIMENSIONS |        |       |       |      |      |
|------------|--------|-------|-------|------|------|
| DIM        | INCHES |       | MM    |      | NOTE |
| DIIVI      | MIN    | MAX   | MIN   | MAX  | NOTE |
| Α          | 0.053  | 0.069 | 1.35  | 1.75 |      |
| В          | 0.004  | 0.010 | 0.10  | 0.25 |      |
| С          | 0.053  | 0.061 | 1.35  | 1.55 |      |
| D          | 0.013  | 0.020 | 0.33  | 0.51 |      |
| E          | 0.007  | 0.010 | 0.17  | 0.25 |      |
| F          | 0.185  | 0.200 | 4.70  | 5.10 |      |
| G          | 0.050  |       | 1.270 |      | TYP. |
| Н          | 0.228  | 0.244 | 5.80  | 6.20 |      |
| J          | 0.150  | 0.157 | 3.80  | 4.00 |      |
| K          | 0.016  | 0.050 | 0.40  | 1.27 |      |
| θ          | 0°     | 8°    | 0°    | 8°   |      |

#### Suggested Solder Pad Layout



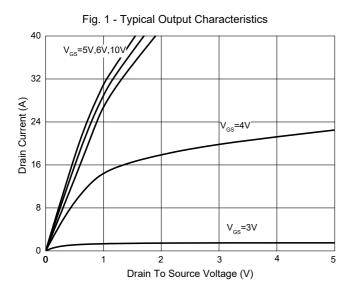


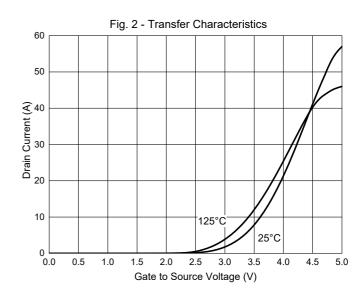
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

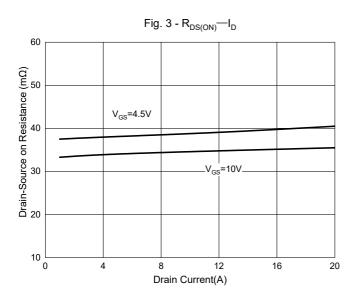
| Parameter                       | Symbol               | Test Conditions   | Min | Тур | Max  | Unit |  |
|---------------------------------|----------------------|---|-----|-----|------|------|--|
| Static Characteristics          | <u> </u>             |   |     |     | •    |      |  |
| Drain-Source Breakdown Voltage  | V <sub>(BR)DSS</sub> | $V_{GS}$ =0V, $I_{D}$ =250 $\mu$ A                                  | 60  |     |      | V    |  |
| Gate-Source Leakage Current     | I <sub>GSS</sub>     | V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V                          |     |     | ±100 | nA   |  |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>     | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                           |     |     | 1    | μA   |  |
| Gate-Threshold Voltage          | V <sub>GS(th)</sub>  | $V_{DS}=V_{GS}$ , $I_{D}=250\mu A$                                  | 1   | 1.5 | 2.5  | V    |  |
| Drain-Source On-Resistance      |                      | V <sub>GS</sub> =10V, I <sub>D</sub> =5A                            |     | 35  | 44   | mΩ   |  |
|                                 | R <sub>DS(on)</sub>  | V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A                           |     | 39  | 49   | mΩ   |  |
| Diode Characteristics           | -                    |   | ,   |     |      |      |  |
| Continuous Body Diode Current   | Is                   |   |     |     | 5    | Α    |  |
| Diode Forward Voltage           | V <sub>SD</sub>      | V <sub>GS</sub> =0V, I <sub>S</sub> =5A                             |     | 0.8 | 1.2  | V    |  |
| Reverse Recovery Time           | t <sub>rr</sub>      | 1 -24 di/dt-E004/up   |     | 45  |      | ns   |  |
| Reverse Recovery Charge         | Q <sub>rr</sub>      | I <sub>F</sub> =2A, di/dt=500A/us                                   |     | 23  |      | nC   |  |
| Dynamic Characteristics         | •                    |   |     |     |      |      |  |
| Input Capacitance               | C <sub>iss</sub>     |   |     | 800 |      |      |  |
| Output Capacitance              | C <sub>oss</sub>     | $V_{DS}$ =30V, $V_{GS}$ =0V,f=1MHz                                  |     | 72  |      | pF   |  |
| Reverse Transfer Capacitance    | C <sub>rss</sub>     |   |     | 38  |      |      |  |
| Total Gate Charge               | $Q_g$                |   |     | 15  |      |      |  |
| Gate-Source Charge              | Q <sub>gs</sub>      | $V_{DS}$ =30V, $V_{GS}$ =10V, $I_{D}$ =5A                           |     | 2.4 |      | nC   |  |
| Gate-Drain Charge               | $Q_{gd}$             |   |     | 2.5 |      |      |  |
| Turn-On Delay Time              | t <sub>d(on)</sub>   |   |     | 5   |      |      |  |
| Turn-On Rise Time               | t <sub>r</sub>       | $V_{GS}$ =10V, $V_{DD}$ =30V,<br>$I_{D}$ =2A, $R_{L}$ =1 $\Omega$ , |     | 39  |      | ns   |  |
| Turn-Off Delay Time             | t <sub>d(off)</sub>  | $R_{GEN}=3\Omega$   |     | 19  |      |      |  |
| Turn-Off Fall Time              | t <sub>f</sub>       |   |     | 7   |      |      |  |

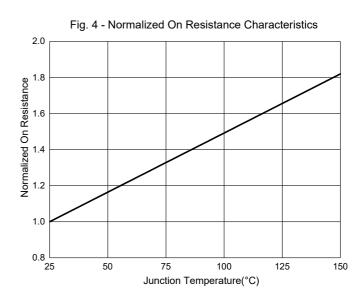


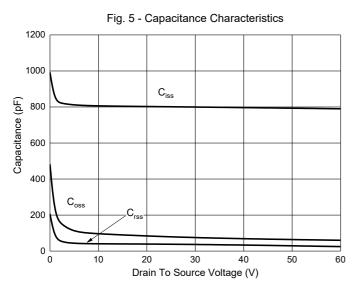
#### **Curve Characteristics**

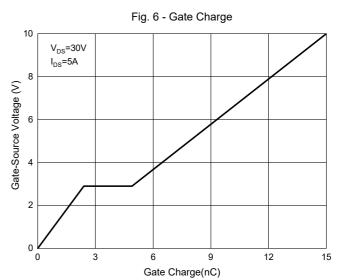






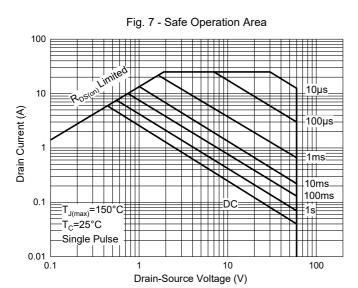








## **Curve Characteristics**





## **Ordering Information**

| Device         | Packing               |  |
|----------------|-----------------------|--|
| Part Number-TP | Tape&Reel: 4Kpcs/Reel |  |

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